

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions of claims in the application.

Listing of Claims

Claim 1 (currently amended): A resist pattern thickening material comprising:

a resin;

a crosslinking agent;

a nitrogen-containing compound; and

pure water; and

a nonionic surfactant which is at least one of a polyoxyethylene-polyoxypropylene condensation product, polyoxyalkylene alkylether compound, a polyoxyethylene alkylether compound, a sorbitan fatty acid ester compound, a glycerin fatty acid ester compound, a primary alcohol ethoxylate compound, a phenol ethoxylate compound, an alkoxylate surfactant, a fatty acid ester surfactant, an amide surfactant, an alcohol surfactant, and an ethylene diamine surfactant,

wherein the nitrogen-containing compound is one of amine, amide, imide, quaternary ammonium, and a derivative thereof,

wherein the resin is at least one of polyvinyl alcohol, polyvinyl acetal, and polyvinyl acetate.

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Claim 2 (original): A resist pattern thickening material according to Claim 1, wherein the nitrogen-containing compound is a basic compound.

Claim 3 (cancelled)

Claim 4 (original): A resist pattern thickening material according to Claim 1, wherein the resist pattern thickening material exhibit at least one of water-solubility and alkali-solubility.

Claims 5-8 (cancelled)

Claim 9 (original): A resist pattern thickening material according to Claim 1, wherein the crosslinking agent is at least one of a melamine derivative, a urea derivative, and an uril derivative.

Claims 10 and 11 (cancelled)

Claim 12 (original): A resist pattern thickening material according to Claim 1, further comprising a resin containing an aromatic compound in a portion thereof.

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Claim 13 (previously presented): A resist pattern thickening material comprising:

a first resin;

a crosslinking agent;

a nitrogen-containing compound;

pure water; and

a second resin containing an aromatic compound in a portion thereof,

wherein the second resin containing the aromatic compound in a portion thereof is at least one of a polyvinyl aryl acetal resin, a polyvinyl aryl ether resin, and a polyvinyl aryl ester resin.

Claim 14 (original): A resist pattern thickening material according to Claim 1, further comprising an organic solvent.

Claim 15 (original): A resist pattern thickening material according to Claim 14, wherein the organic solvent is at least one of an alcohol solvent, a chain ester solvent, a cyclic ester solvent, a ketone solvent, a chain ether solvent, and a cyclic ether solvent.

Claim 16 (currently amended): A resist pattern comprising:

an inner layer of a resist pattern; and

a surface layer of a resist pattern provided on the inner layer, the surface layer being a resist pattern thickening material comprising:

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a resin;

a crosslinking agent;

a nitrogen-containing compound;

pure water; and

a nonionic surfactant which is at least one of a polyoxyethylene-polyoxypropylene condensation product, polyoxyalkylene alkylether compound, a polyoxyethylene alkylether compound, a sorbitan fatty acid ester compound, a glycerin fatty acid ester compound, a primary alcohol ethoxylate compound, a phenol ethoxylate compound, an alkoxylate surfactant, a fatty acid ester surfactant, an amide surfactant, an alcohol surfactant, and an ethylene diamine surfactant,

wherein the nitrogen-containing compound is one of amine, amide, imide, quaternary ammonium, and a derivative thereof,

wherein the resin is at least one of polyvinyl alcohol, polyvinyl acetal, and polyvinyl acetate.

Claim 17 (currently amended): A process for forming a resist pattern, comprising:

applying a resist pattern thickening material onto a resist pattern to be thickened after forming the resist pattern to be thickened so as to cover a surface of the resist pattern to be thickened,

wherein the resist pattern thickening material comprises:

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a resin;

a crosslinking agent;

a nitrogen-containing compound;

pure water; and

a nonionic surfactant which is at least one of a polyoxyethylene-polyoxypropylene condensation product, polyoxyalkylene alkylether compound, a polyoxyethylene alkylether compound, a sorbitan fatty acid ester compound, a glycerin fatty acid ester compound, a primary alcohol ethoxylate compound, a phenol ethoxylate compound, an alkoxylate surfactant, a fatty acid ester surfactant, an amide surfactant, an alcohol surfactant, and an ethylene diamine surfactant,

wherein the nitrogen-containing compound is one of amine, amide, imide, quaternary ammonium, and a derivative thereof,

wherein the resin is at least one of polyvinyl alcohol, polyvinyl acetal, and polyvinyl acetate.

Claim 18 (original): A process for forming a resist pattern according to Claim 17, wherein a material of the resist pattern to be thickened is at least one of a novolak resist, a polyhydroxystyrene (PHS) resist, an acrylic resist, a cycloolefin - maleic acid anhydride resist, a cycloolefin resist, and a cycloolefin - acryl hybrid resist.

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Claim 19 (previously presented): A process for forming a resist pattern according to Claim 17, further comprising:

developing the resist pattern thickening material, after applying the resist pattern thickening material.

Claim 20 (previously presented): A semiconductor device comprising:

a pattern formed by using a resist pattern thickened by using a resist pattern thickening material,

wherein the resist pattern thickening material comprises:

a resin;

a crosslinking agent;

a nitrogen-containing compound;

pure water; and

a nonionic surfactant which is at least one of a polyoxyethylene-polyoxypropylene condensation product, polyoxyalkylene alkylether compound, a polyoxyethylene alkylether compound, a sorbitan fatty acid ester compound, a glycerin fatty acid ester compound, a primary alcohol ethoxylate compound, a phenol ethoxylate compound, an alkoxylate surfactant, a fatty acid ester surfactant, an amide surfactant, an alcohol surfactant, and an ethylene diamine surfactant,

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wherein the nitrogen-containing compound is one of amine, amide, imide, quaternary ammonium, and a derivative thereof,

wherein the resin is at least one of polyvinyl alcohol, polyvinyl acetal, and polyvinyl acetate.

Claim 21 (currently amended): A process for manufacturing a semiconductor device comprising:

applying a resist pattern thickening material onto a resist pattern to be thickened, after the resist pattern to be thickened is formed, so as to thicken the resist pattern to be thickened and form the resist pattern; and

patterning the underlying layer by etching using the resist pattern as a mask so as to pattern the underlying layer,

wherein the resist pattern thickening material comprises:

a resin;

a crosslinking agent;

a nitrogen-containing compound;

pure water; and

a nonionic surfactant which is at least one of a polyoxyethylene-polyoxypropylene condensation product, polyoxyalkylene alkylether compound, a polyoxyethylene alkylether compound, a sorbitan fatty acid ester compound, a glycerin fatty acid ester compound, a primary

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alcohol ethoxylate compound, a phenol ethoxylate compound, an alkoxylate surfactant, a fatty acid ester surfactant, an amide surfactant, an alcohol surfactant, and an ethylene diamine surfactant,

wherein the nitrogen-containing compound is one of amine, amide, imide, quaternary ammonium, and a derivative thereof,

wherein the resin is at least one of polyvinyl alcohol, polyvinyl acetal, and polyvinyl acetate.

Claim 22 (new): A resist pattern thickening material according to claim 1, wherein the nitrogen-containing compound is one of imide, quaternary ammonium, and a derivative thereof.

Claim 23 (new): A resist pattern according to claim 16, wherein the nitrogen-containing compound is one of imide, quaternary ammonium, and a derivative thereof.

Claim 24 (new): A process for forming a resist pattern according to claim 17, wherein the nitrogen-containing compound is one of imide, quaternary ammonium, and a derivative thereof.

Claim 25 (new): A semiconductor device according to claim 20, wherein the nitrogen-containing compound is one of imide, quaternary ammonium, and a derivative thereof.

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Claim 26 (new): A process for manufacturing a semiconductor device according to claim 21, wherein the nitrogen-containing compound is one of imide, quaternary ammonium, and a derivative thereof.